Silicon N-Channel MOS FET

HITACHI

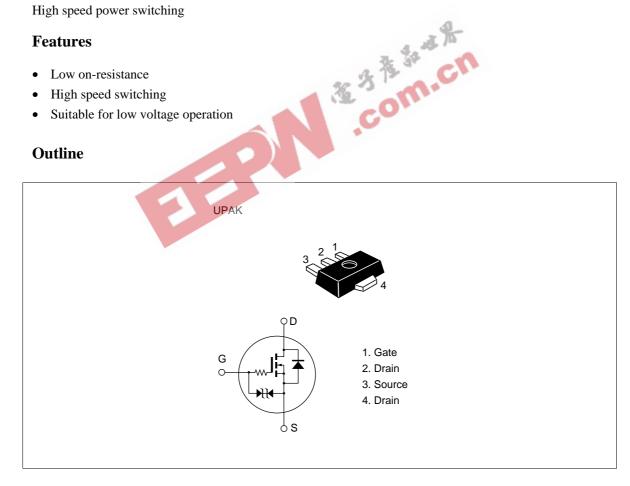
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Suitable for low voltage operation

Outline





Absolute Maximum Ratings (Ta = 25°C unless otherwise specified.)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	12	V
Gate to source voltage	V _{GSS}	±7	V
Drain current	I _D	2	А
Drain peak current	I _{D(pulse)} *1	4	А
Body to drain diode reverse drain current	I _{DR}	2	Α
Channel power dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

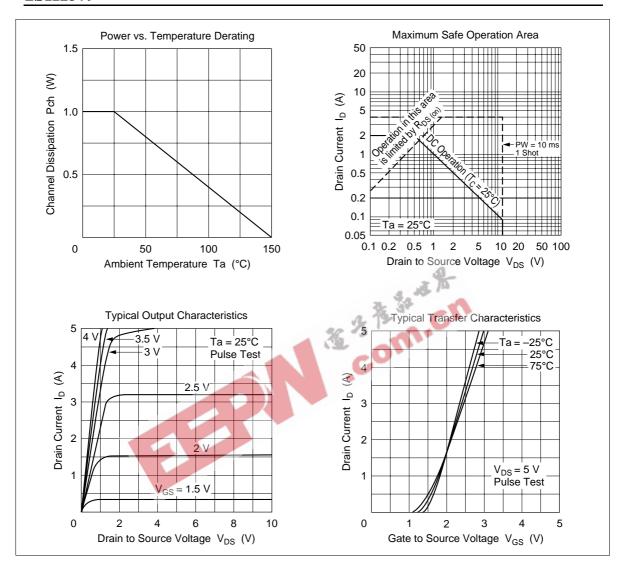
Notes 1. PW \leq 100 μ s, duty cycle \leq 10%

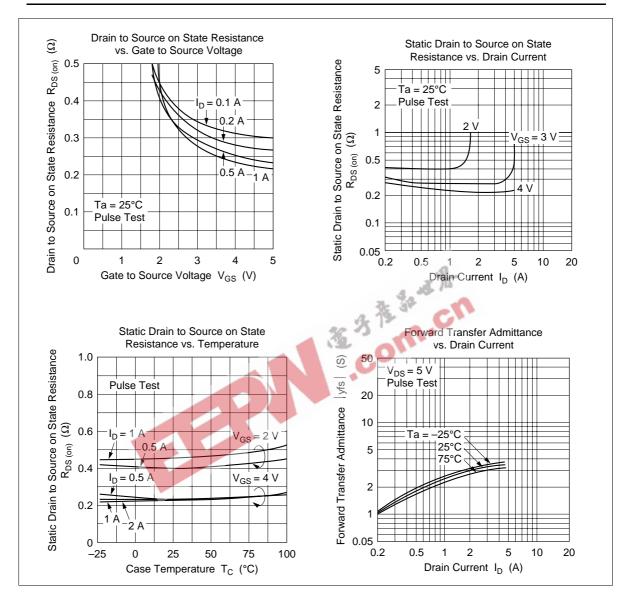
2. Value on the almina ceramic board (12.5 \times 20 \times 0.7 mm)

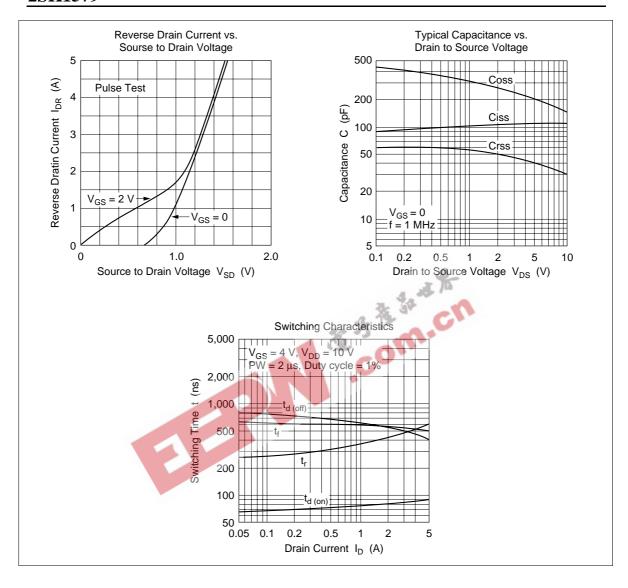


Electrical Characteristics (Ta = 25°C unless otherwise specified.)

Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source cutoff current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 8 \text{ V}, V_{GS} = 0$	
Gate to source cutoff current	I _{GSS}	_	_	±5	μΑ	$V_{GS} = \pm 6.5 \text{ V}, V_{DS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	0.4	_	1.4	V	$V_{DS} = 5 \text{ V}, I_{D} = 100 \mu\text{A}$	
Drain to source on resistance (1)	$R_{\rm DS(on)}1$	_	0.36	0.7	Ω	$V_{GS} = 2.2 \text{ V}, I_{D} = 0.5 \text{ A}$	
Drain to source on resistance (2)	R _{DS(on)} 2	_	0.25	0.35	Ω	$V_{GS} = 4 \text{ V}, I_D = 1 \text{ A}$	
DC forward transfer admittance	yfs	1	2.5	_	S	$V_{DS} = 5 \text{ V}, I_{D} = 1 \text{ A},$ $\Delta V_{GS} = 0.1 \text{ V}$	
Input capacitance	Ciss	_	110	_	pF	$V_{DS} = 5 \text{ V}, V_{GS} = 0,$	
Reverse transfer capacitance	Crss	_	30		pF	f = 1 MHz	
Output capacitance	Coss	_	150	- 36.	pF	n.	
Turn-on time	t _(on)	_	500	3	ns	$I_D = 0.2 \text{ A}, V_{GS} = 0,$	
Turn-off time	$t_{(off)}$	-	1500	-0	ns	Vin = 4 V, $R_L = 51 \Omega$	
Note 1. Marking is "DY".							

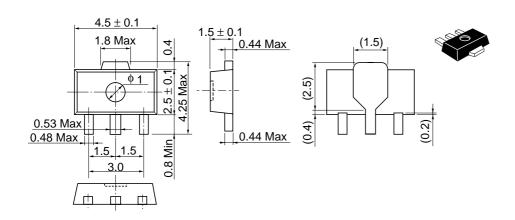








Unit: mm



Hitachi Code	UPAK
JEDEC	_
EIAJ	Conforms
Weight (reference value)	0.050 g

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